

General Description

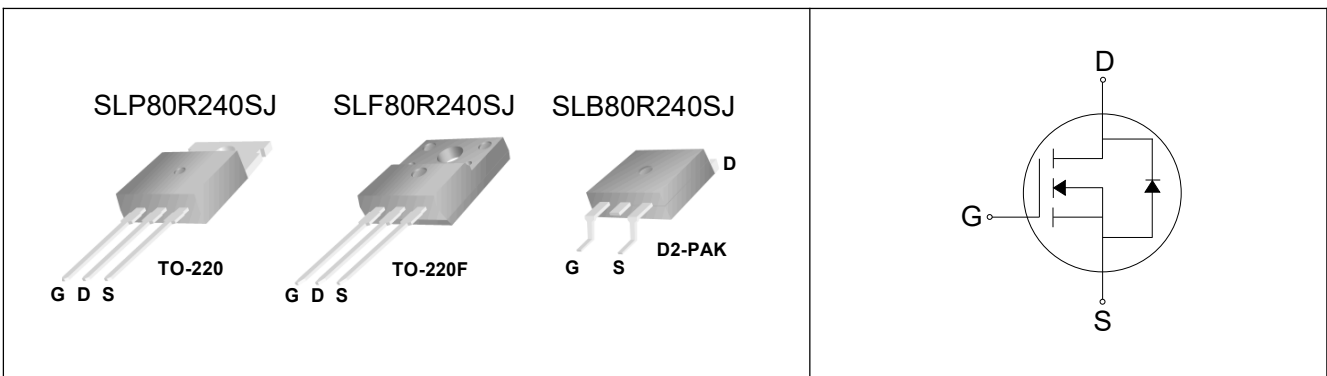
This Power MOSFET is produced using Maple semi's Advanced Super-Junction technology.

This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for AC/DC power conversion

Features

- 20A, 800V, $R_{DS(on)}$ typ. = $0.22\Omega @ V_{GS} = 10V$
- Low gate charge (typical 70nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	D2PAK/TO-220	TO-220F	Units
VDSS	Drain-Source Voltage	800		V
ID	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	20	20*
		- Continuous ($T_C = 100^\circ\text{C}$)	10	10*
IDM	Drain Current - Pulsed (Note 1)	62	62*	A
VGSS	Gate-Source Voltage	± 30		V
EAS	Single Pulsed Avalanche Energy (Note 2)	485		mJ
IAR	Avalanche Current (Note 1)	20		A
EAR	Repetitive Avalanche Energy (Note 1)	1		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
PD	Power Dissipation ($T_C = 25^\circ\text{C}$)	205	35	W
		- Derate above 25°C	1.7	0.3
TJ, TSTG	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	Value			Units
		TO-220	D2PAK	TO-220F	
R θ JC	Thermal Resistance, Junction-to-Case	0.6	0.6	3.6	$^\circ\text{C}/\text{W}$
R θ JS	Thermal Resistance, Case-to-Sink Typ.	0.5	0.5	-	$^\circ\text{C}/\text{W}$
R θ JA	Thermal Resistance, Junction-to-Ambient	62	62	80	$^\circ\text{C}/\text{W}$

Electrical Characteristics (TC = 25 °C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BVDSS	Drain-Source Breakdown Voltage	VGS = 0V, ID = 250uA, TJ=25°C	800	-	-	V
		VGS = 0V, ID = 250uA, TJ=150°C	-	850	-	V
Δ BVDSS Δ TJ	Breakdown Voltage Temperature coefficient	ID = 250uA, referenced to 25°C	-	0.6	-	V/°C
IDSS	Drain-Source Leakage Current	VDS =800V, VGS = 0V	-	-	1	uA
		VDS =640V, TC = 125 °C	-	-	10	uA
IGSS	Gate-Source Leakage, Forward	VGS = 30V, VDS = 0V	-	-	100	nA
	Gate-source Leakage, Reverse	VGS = -30V, VDS = 0V	-	-	-100	nA
On Characteristics						
VGS(th)	Gate Threshold Voltage	VDS = VGS, ID = 250uA	2.5	3.5	4.5	V
RDS(ON)	Static Drain-Source On-state Resistance	VGS =10 V, ID = 10A	-	0.22	0.24	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	VGS =0 V, VDS =25V, f = 1MHz	-	1440	-	pF
Coss	Output Capacitance		-	300	-	
Crss	Reverse Transfer Capacitance		-	10	-	
Dynamic Characteristics						
td(on)	Turn-on Delay Time	VDD =400V, ID =10A, RG =20 Ω	-	25	-	nS
tr	Rise Time		-	55	-	
td(off)	Turn-off Delay Time		-	70	-	
tf	Fall Time		-	40	-	
Qg	Total Gate Charge	VDS =480V, VGS =10V, ID =10A	-	70	-	nC
Qgs	Gate-Source Charge		-	7.8	-	
Qgd	Gate-Drain Charge(Miller Charge)		-	9	-	

Source-Drain Diode Ratings and Characteristics

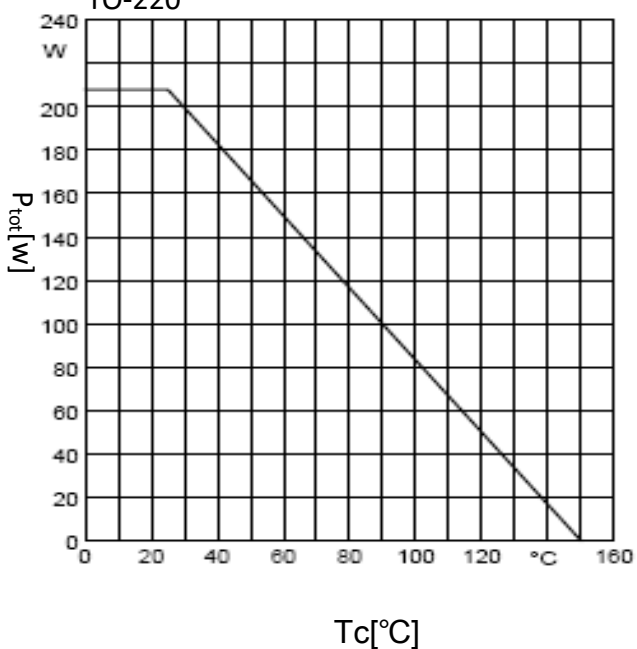
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit.
IS	Maximum Continuous Drain-Source Diode Forward Current		-	-	20	A
ISM	Maximum Pulsed Drain-Source Diode Forward Current		-	-	60	
VSD	Diode Forward Voltage	IS =10A, VGS =0V	-	1	1.5	V
trr	Reverse Recovery Time	IS =10A, VGS=0V, dIF/dt=100A/us	-	475	-	nS
Qrr	Reverse Recovery Charge		-	5.8	-	uC

NOTES

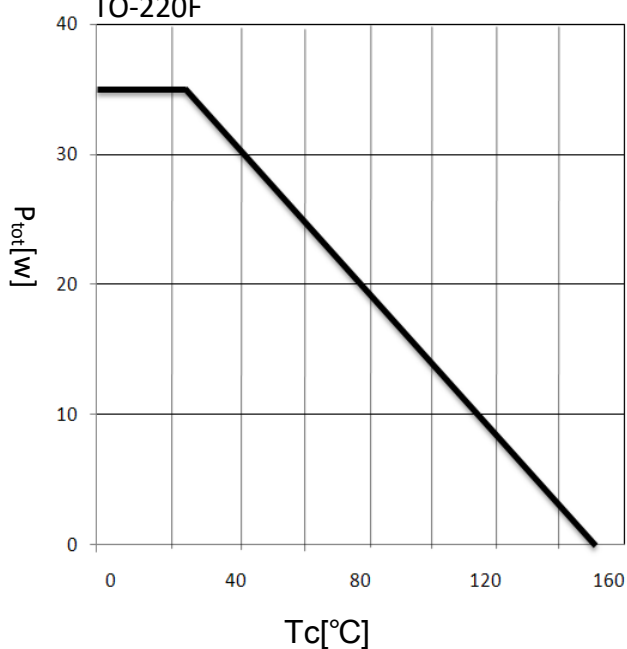
1. Repeativity rating : pulse width limited by junction temperature
2. L =79mH, IAS =3.5A, VDD = 50V, RG = 25 Ω , Starting TJ = 25°C
3. ISD \leq ID, di/dt \leq 200A/us, VDD \leq BVDSS, Starting TJ = 25°C
4. Pulse Test : Pulse Width \leq 300us, Duty Cycle \leq 2%
5. Essentially independent of operating temperature.

Typical Performance Characteristics

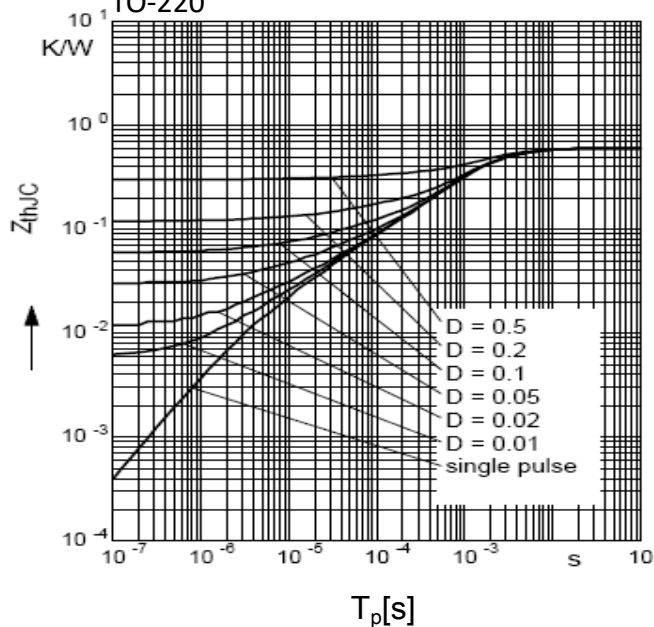
Power dissipation
TO-220



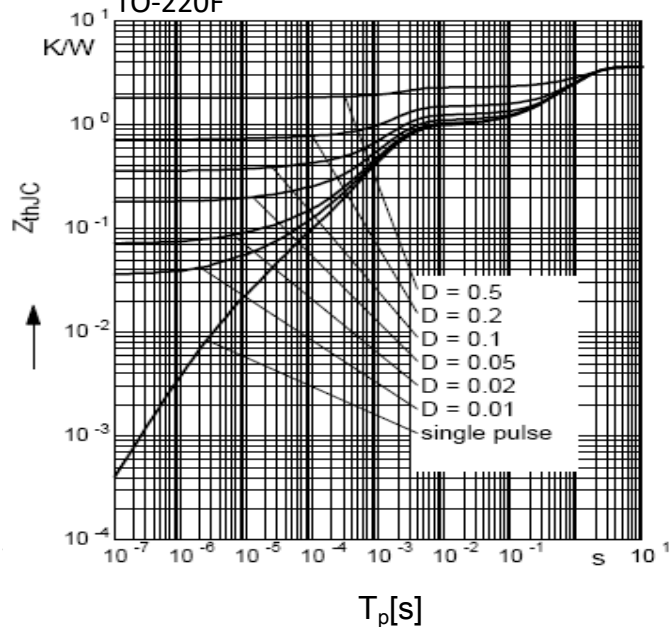
Power dissipation
TO-220F



Max. transient thermal impedance
TO-220

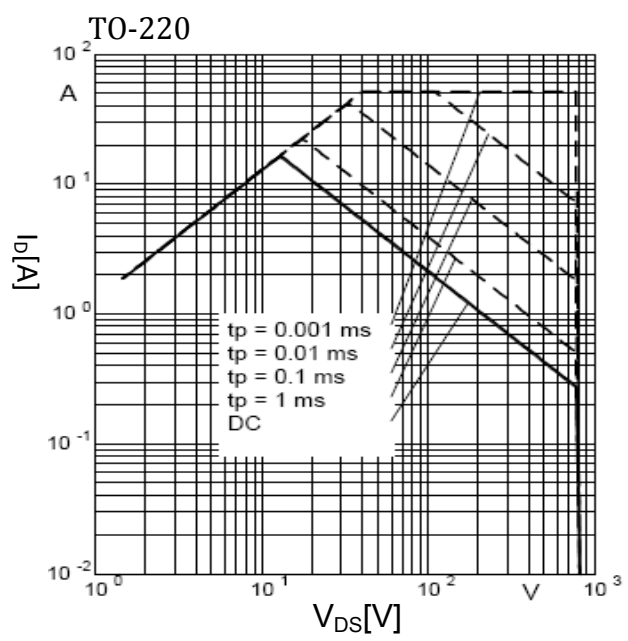


Max. transient thermal impedance
TO-220F

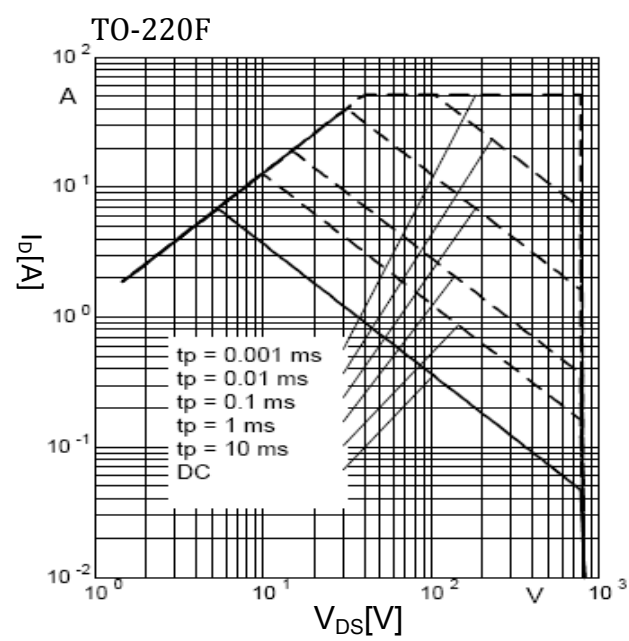


Typical Performance Characteristics

Safe operating area $TC=25\text{ }^{\circ}\text{C}$

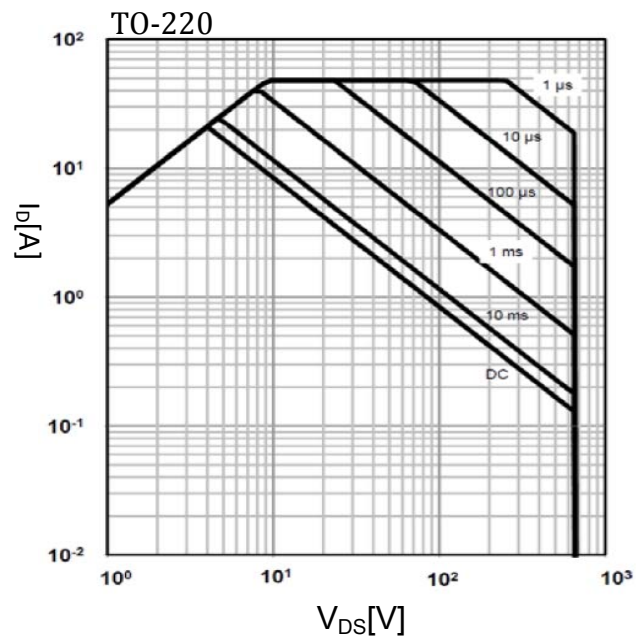


Safe operating area $TC=25\text{ }^{\circ}\text{C}$

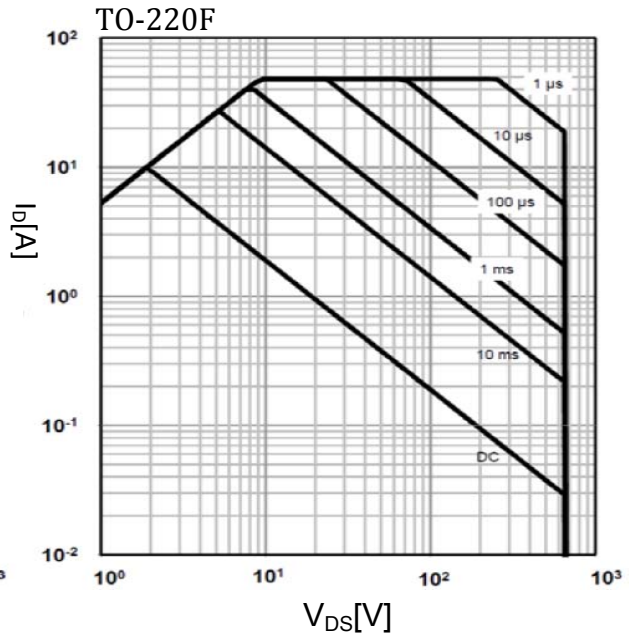


$I_D=f(V_{DS}); TC=25\text{ }^{\circ}\text{C}; V_{GS} > 7V; D=0; \text{parameter } t_p$

Safe operating area $TC=80\text{ }^{\circ}\text{C}$



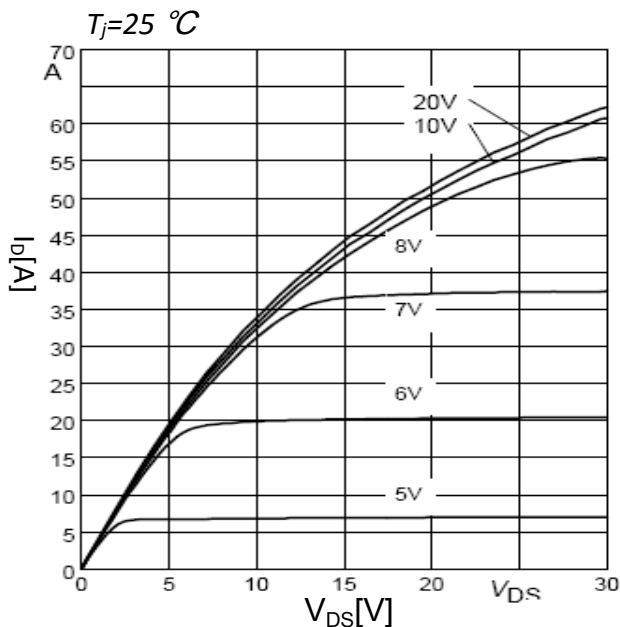
Safe operating area $TC=80\text{ }^{\circ}\text{C}$



$I_D=f(V_{DS}); TC=80\text{ }^{\circ}\text{C}; V_{GS} > 7V; D=0;$
 parameter t_p

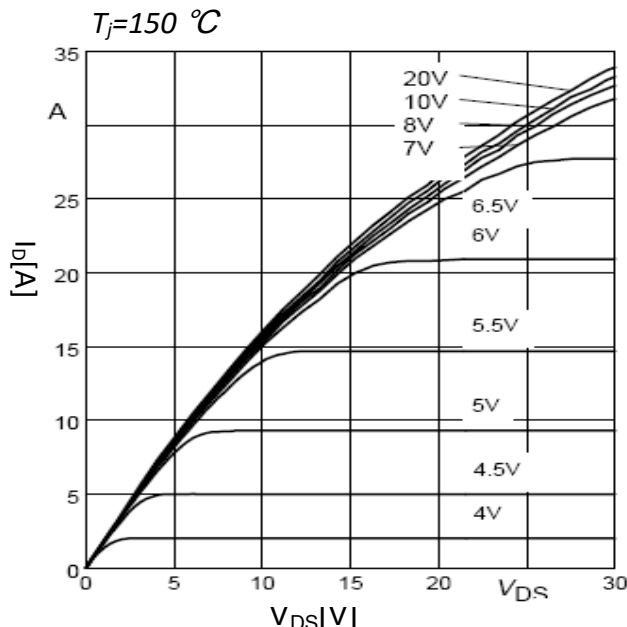
Typical Performance Characteristics

Typ. output characteristics

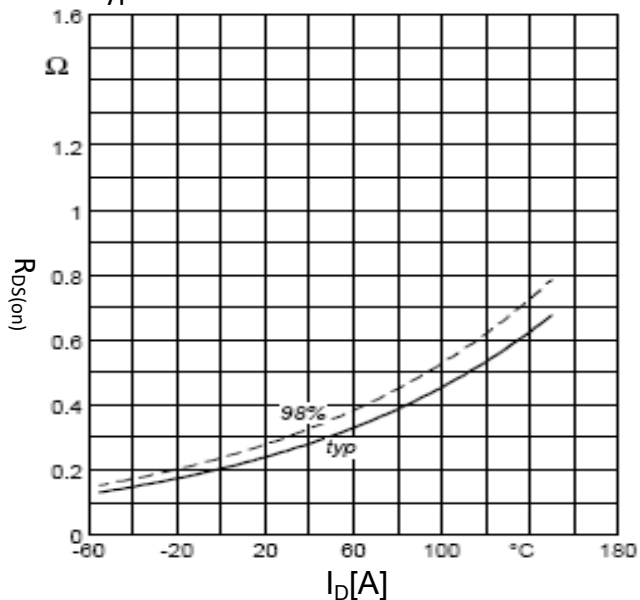


$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C}; \text{parameter: } V_{GS}$

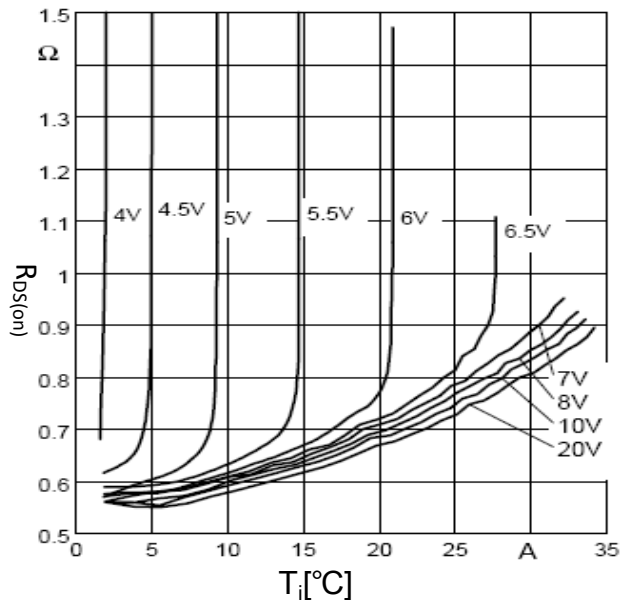
Typ. output characteristics



Typ. drain-source on-state resistance



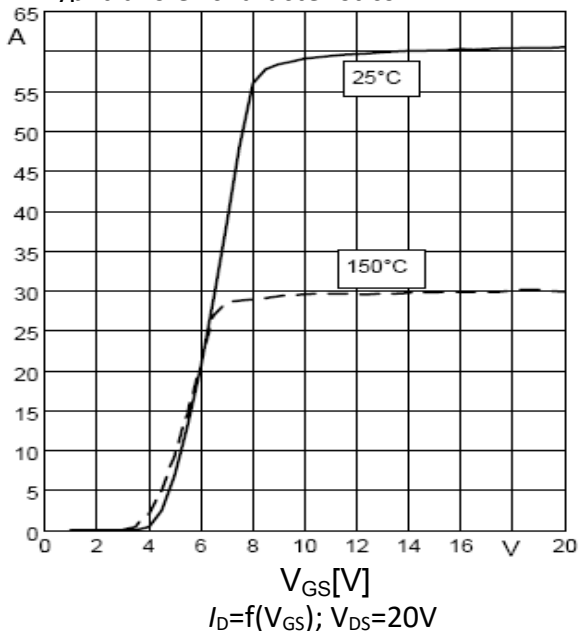
$R_{DS(on)}=f(I_D); T_j=150\text{ }^\circ\text{C}; \text{parameter: } V_{GS}$



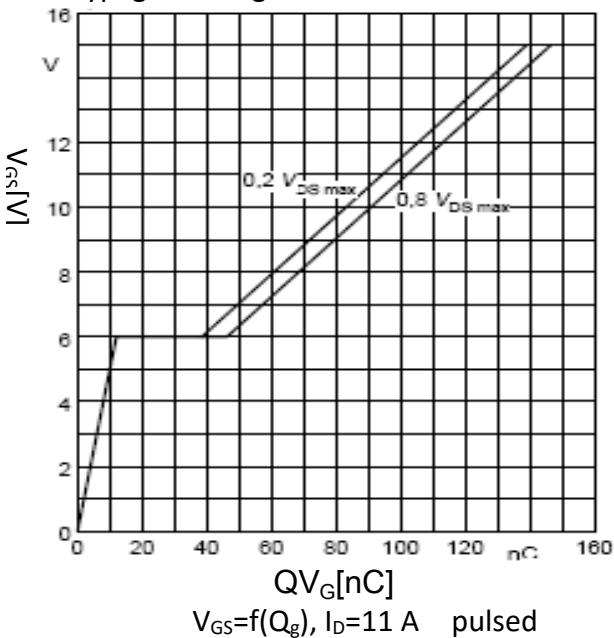
$R_{DS(on)}=f(T_j); I_D=11\text{ A}; V_{GS}=10\text{ V}$

Typical Performance Characteristics

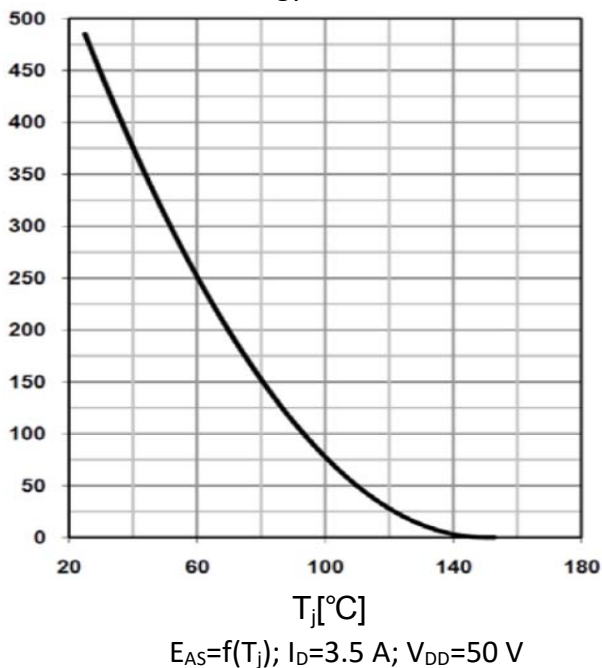
Typ. transfer characteristics



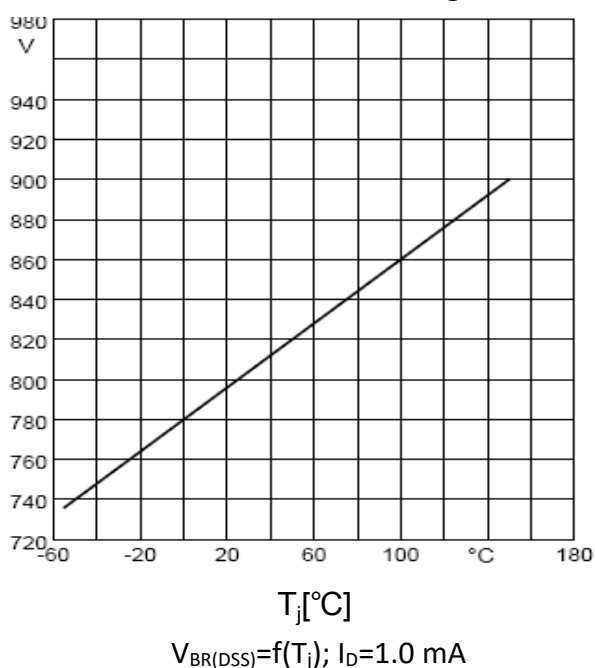
Typ. gate charge



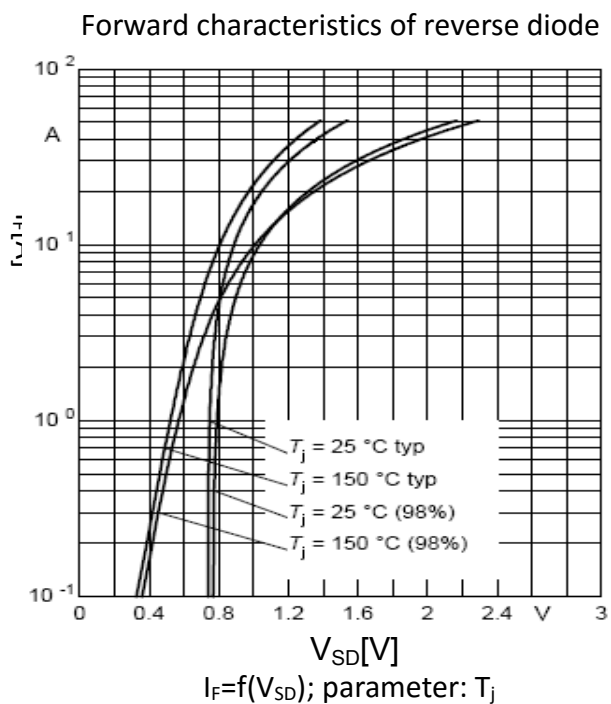
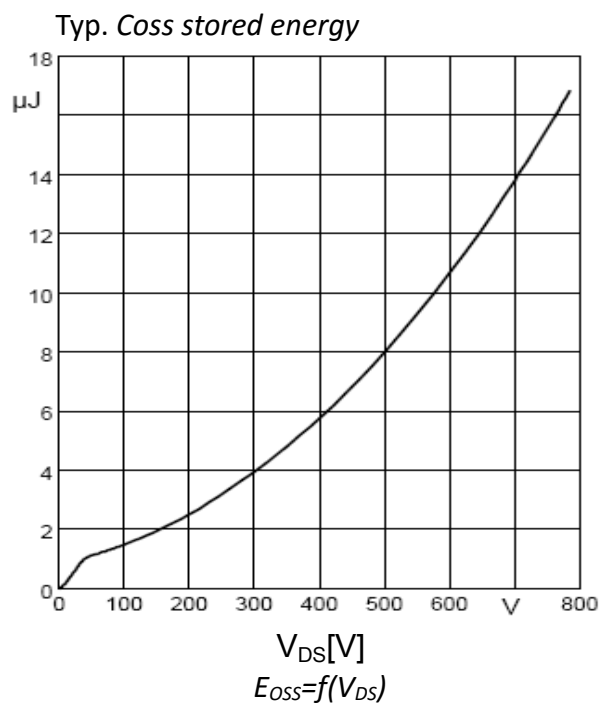
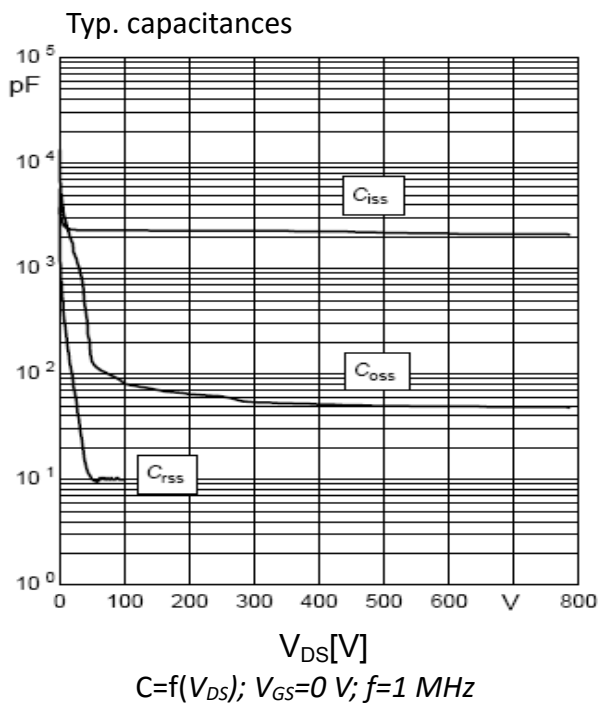
Avalanche energy



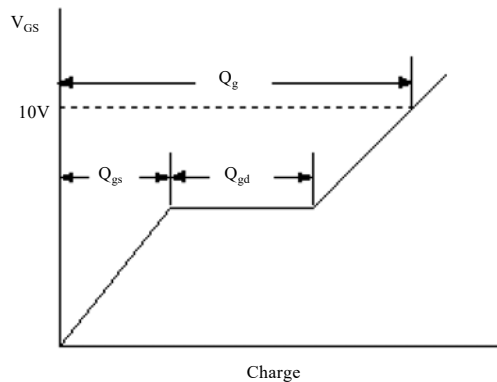
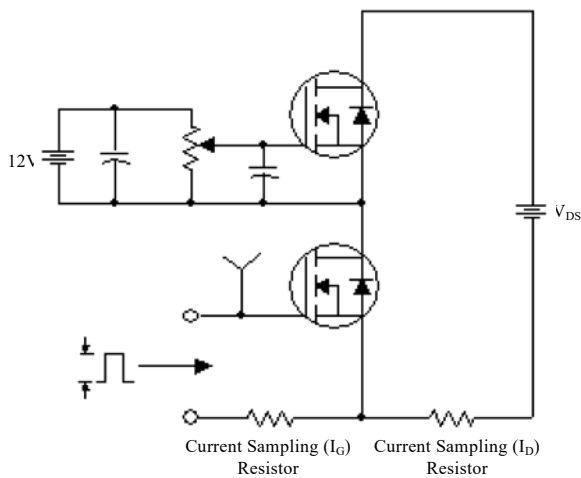
Drain-source breakdown voltage



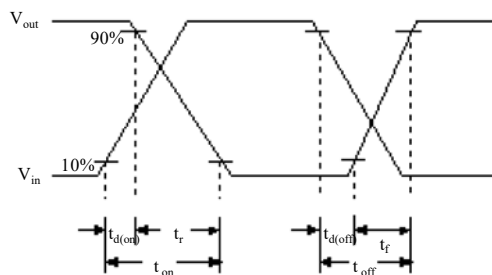
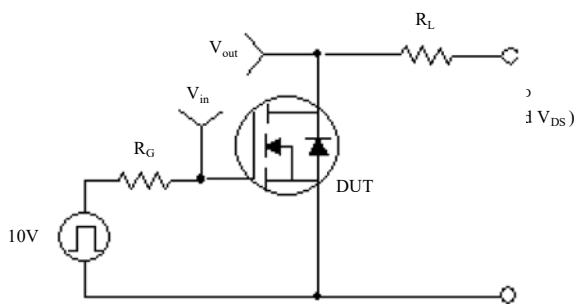
Typical Performance Characteristics



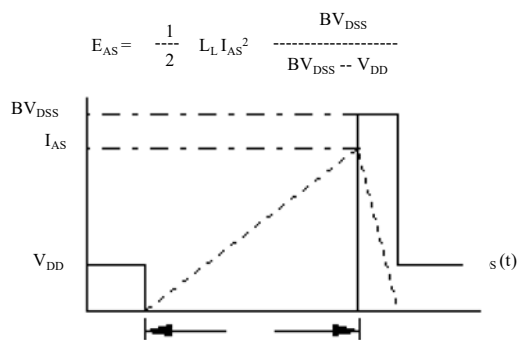
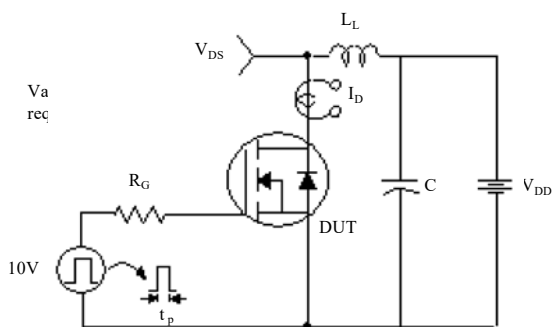
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms

